

3. (Amended) A group III nitride compound semiconductor device of a successively laminated structure comprising:

a substrate;

a buffer layer;

a first layer formed of $\text{Al}_a\text{Ga}_b\text{In}_{1-a-b}\text{N}$ ($0 < a < 1$, $0 < b < 1$, $a+b < 1$); and

a second layer formed of $\text{In}_Y\text{Ga}_{1-Y}\text{N}$ ($0 < Y < 1$);

wherein said buffer layer is disposed between and in direct contact with both said substrate and said first layer, and said first layer is disposed between and in direct contact with both said buffer layer and said second layer.

See the attached Appendix for the changes made to effect the above claims.